

Index

a

ab initio 259, 260, 261, 266, 272–275, 279, 282

Ab Initio Modelling PROgram.

see AIMPRO

acceptor 183–185, 188–196

AIMPRO (*Ab Initio* Modelling PROgram) 285, 286, 289, 290, 292

alignment 118, 120, 122, 248, 256

alignment potential 172, 174, 364, 366

aluminium 260, 261, 279, 280, 282

amorphous silica 201, 210

amorphous states 205, 207

anharmonic excitations 259, 278–282

b

backflow 19, 22, 25, 26, 28, 29

band alignment 34, 219–220

band edges/band extrema, valence band maximum (VBM)/conduction band minimum (CBM) 119, 123, 124

band gap 79, 80, 82–85, 88–93, 98–108, 115, 307, 313, 318, 319

band gap underestimate 362, 367

band offsets 33, 48, 49, 118, 128

band structure 79, 80, 82–85, 89–91, 93, 168–171, 178, 359, 360, 371

band-gap problem 6–13, 112, 120, 121

barrier (Energy-) 194, 195, 197

benzene 69

Bethe-Salpeter equation (BSE) 353, 362, 372

BiFeO₃ 83, 92, 93

bipolar doping 213, 214

bloch (wave) function 306, 312, 313, 321, 330

c

calculation 79, 80, 84, 85, 88, 89, 91–93

carbon (diamond) 23, 24

Car-Parrinello method 72

central cell correction 306, 322, 324, 333

charge localization 252

charge state 131, 315, 318–320

charge transition level 113, 114, 118–125, 129–132, 140, 144–146, 253

chemical potential 4, 9, 214, 220–223, 237

co-doping 229, 232–235

coherence time 342

compensation 83

concentration 1–4

configuration coordinate diagram 194, 195

constant pressure approach 260–262, 264–266, 279, 281

convergence 116

correlated materials 104, 108

d

d states 7, 8, 10–13

dangling bond 129

deep defect 305, 306, 312, 319, 320, 324, 335

deep level, -state 183, 189, 195, 196, 207–209

defect energy levels 33

defect formation energies 54, 86, 92, 214, 224

defect localized state 193

defect 79, 81, 82–89, 91, 92, 201, 207–209

density functional 183, 185

density functional theory (DFT) 17, 33, 34, 37–41, 48–52, 55–57, 79, 97–100, 155, 259, 281, 301, 305–307, 329, 330, 332, 341, 346

density of states (DOS) 310, 312, 319, 325

diamond 342, 343, 345, 351, 353–356

dielectric constant 249

diffusion 1, 4, 12, 131

Diffusion Monte Carlo (DMC) 17
 Dirac's equation 308, 309
 disordered tetrahedral networks 201
 divacancy 342, 344, 345, 346, 353–356
 doping asymmetry 213
 doping limit rule 214, 218, 219
 doping 83
 Dyson's equation 311, 312, 314, 324,
 326, 327, 332

e

effective mass approximation (EMA) 306,
 319–324, 330, 336, 363
 EL2 317, 319
 electrically detected magnetic resonance
 (EDMR) 328
 electron nuclear double resonance
 (ENDOR) 319, 322, 324–326
 electron paramagnetic resonance (EPR) 178,
 320, 322, 333, 334
 electronic excitations 266, 269, 270
 electronic properties 33
 electronic structure 83, 107, 201, 202,
 204–206, 209
 electrostatic interactions 241, 247, 255
 energy levels of neutral atom 227
 entropy of defect formation 281, 282
 exchange-correlation 37, 38, 52
 exchange-correlation functional 259–261,
 279
 excitation energy 140
 exciton binding energy 352–355
 excitonic 373, 375
 expansion coefficient 279, 280

f

filter diagonalisation 292, 299
 finite size corrections 172, 173, 176, 178
 finite size effects 29, 363, 366
 fixed-node approximation 19, 22, 25, 26
 formation energies (defect formation
 energies) 2–6, 8–12, 113, 122, 249, 259,
 261, 279, 282
 free energy 259–270, 272–279, 281, 282
 free energy Born-Oppenheimer
 approximation 266–269
 functional 359, 362, 368–374

g

GaAs 196, 313, 315
 GaN 195–197
 gap correction to levels 143
 gap correction to total energy 143
 gap error 139–141, 143–146, 151, 152

gap level 141, 143–148, 150
 Generalized Koopman's Theorem 371
 generalized-gradient approximation
 (GGA) 17, 18
 graphitic systems 105
 Green's Function 2, 305, 306, 311–317,
 320, 324, 327, 328, 330, 333, 334, 359,
 360, 365–368, 374
 group IV semiconductors 149
 group theory 342, 344, 353, 354
 GW 12, 24, 128, 141, 143, 146, 152, 165,
 168, 169–171, 178
 GW approximation 34, 36–38, 40,
 61–64, 202, 204, 362
 GW method 352

h

Hafnium oxide 121
 Hartree-Fock method 184
 H-assisted doping 223–224
 heat capacity 279, 280
 HfO₂ 83, 91, 92
 hole-state potential 184, 188–190
 HSE (Heyd, Scuseria, and Ernzerhof)
 hybrid functional 97–108, 149, 156,
 158, 159, 160, 162
 hybrid 362, 367–374
 hybrid density-functional 216
 hybrid functional(s) 9–11, 13, 18, 29, 80,
 112, 114, 125, 133, 134, 142, 144–146,
 148, 165, 167, 178, 184, 185, 187,
 189–193, 341, 350, 352, 354
 hybrid scheme 215
 hyperfine interaction 342

i

imaginary time step 20, 28
 impurities 155, 161, 162
 impurity-band 232, 234, 236
 interface properties 33–57
 inverse participation ratio 76
 ionization potential 69–70

j

Jahn-Teller distortion 355
 Janak's theorem 185, 186
 Jastrow factor 19

k

Kohn-Luttinger oscillation 328, 336
 Kohn-Sham formalism of density functional
 theory (KSDFT) 285, 286, 288,
 292, 301
 Koopman's theorem 187, 216

Koopman's Condition 185–188, 191, 193, 196
 KSDFT (Kohn-Sham-formalism of density functional theory) 285, 292, 299, 301

I

large-scale calculations 299, 301
 lattice relaxation 306, 313, 314, 317, 319, 326, 327
 LDA+*U* 6–9, 165–180
 linear elasticity theory 328–330, 332
 linear muffin-tin orbital (LMTO) 313–315, 323, 324
 local density approximation (LDA) 155, 165, 307, 313, 361
 local field effects 204, 209
 local moment counter charge 366
 local spin density approximation (LSDA) 17, 18, 23, 25, 27, 305, 307, 308, 310, 325, 330
 localization (electron- or hole-) 194, 197
 localized states 121

m

magnesium oxide 23, 25
 magnetic field 306, 308
 magnetic ordering 107
 magnetization density 307, 309, 310, 312, 314–316, 318, 320–322, 325, 331, 335
 Makov and Payne correction 216, 242
 Makov Payne quadrupole correction 364
 many-body perturbation theory (MBPT) 34–38, 61
 Mg-acceptor 195
 modified pseudopotentials 12, 13
 molecular doping 220, 222–223, 237
 molecular dynamics 272, 274, 277
 molecular dynamic (MD) simulation 333, 334
 Mott insulators 106

n

neutralizing background 246
 neutron transmutation 332, 334
 nitrogen-vacancy center (NV center) 342, 351

o

optical gaps 100–102
 optimal polarizability basis 61–68
 oxidation 131
 oxygen vacancy 165, 173, 174, 179, 180

p

periodic boundary conditions 97
 perturbed host state 194
 phase stability 105, 106
 photoluminescence 342
 point defects 17, 18, 72, 155, 156, 158, 159, 161, 259–261, 277, 278
 polaron 183, 188–190
 potential alignment 248, 256
 projector-augmented wave (PAW) 34
 pseudopotential 19, 22–26, 28, 313–315, 320, 322–327
 pseudopotential locality approximation 28

q

quantum bit 342, 356
 quantum communication 342
 Quantum Monte Carlo (QMC) 18, 19
 quantum-espresso 68
 quasiharmonic approximation 271, 273
 quasiparticle 62, 362, 367, 370, 372, 375
 quasiparticle corrections 34

r

Random Phase Approximation (RPA) 63
 rare earths 106
 relative energy of different configurations 144
 relativistic 308, 309
 resonances 147, 148, 152

s

sawtooth 249
 Schottky defect 23, 25
 scissor operator 142, 143
 screened exchange 100, 103, 104, 134, 369, 371
 screened hybrids 100, 103, 104
 screening 243
 self-interaction 184, 186
 self-interaction error 361, 362, 370
 self-interstitial 18, 23, 25
 self-trapped polaron 370
 semiconductor devices (or electronic devices) 131
 shallow defect 363, 366, 367, 374
 shallow donors 306, 322, 324, 333, 334, 336
 shallow level, -state 183, 189, 195, 196
 SiC 306, 313, 319, 320, 322, 332–336
 silica 70, 201, 202, 210
 silicon (Si) 121, 130, 306, 310, 313, 322, 325, 328, 331–336

silicon carbide 342, 344, 353
 silicon nitride (vitreous) 72–77
 silicon oxide/silicon dioxide (SiO₂)
 120, 131
 silicon(bulk) 18, 25, 26, 28, 70,
 105, 106
 solid state calculations 97
 Space-Time method (STM) 63
 spin-orbit interaction 309
 Stokes shift 346, 347, 353, 355
 supercell 183, 184, 189
 supercell correction 246
 supercell geometry 2, 5
 supercell-size convergence 3
 surfactant 220, 224–226, 237
 symmetry and occupation of defect
 levels 217

t

thermodynamic integration 272–277
 thermodynamics 262, 266, 271–277
 time-dependent density functional theory
 (TD-DFT) 346–351
 TiO₂ 10, 11

transition energy level 213–215, 229
 transition levels 3–5, 7–12

u

universal approaches 232
 UP-TILD method 275, 276

v

vacancy 4, 8–11, 23–25, 251
 vacancy concentration 281, 282
 vertex corrections 51–54
 voronoi cell/tessellation 314, 316–318, 324

w

Wannier's functions 64–67
 wave function 250, 252
 wide band gap oxides 92, 93

z

zero-variance extrapolation 29
 zinc oxide (ZnO) 4, 6–12, 79, 83–90, 124,
 165, 167–171, 173, 176, 177, 183–185,
 188–191, 193–196, 213–214, 220–237
 ZnTe 196